VRW056 ṂṂ Ḷ SQS ÆṀ ɥ s ǁ ˥ Silicon PNP transistor in a SOT-23 Plastic Package.

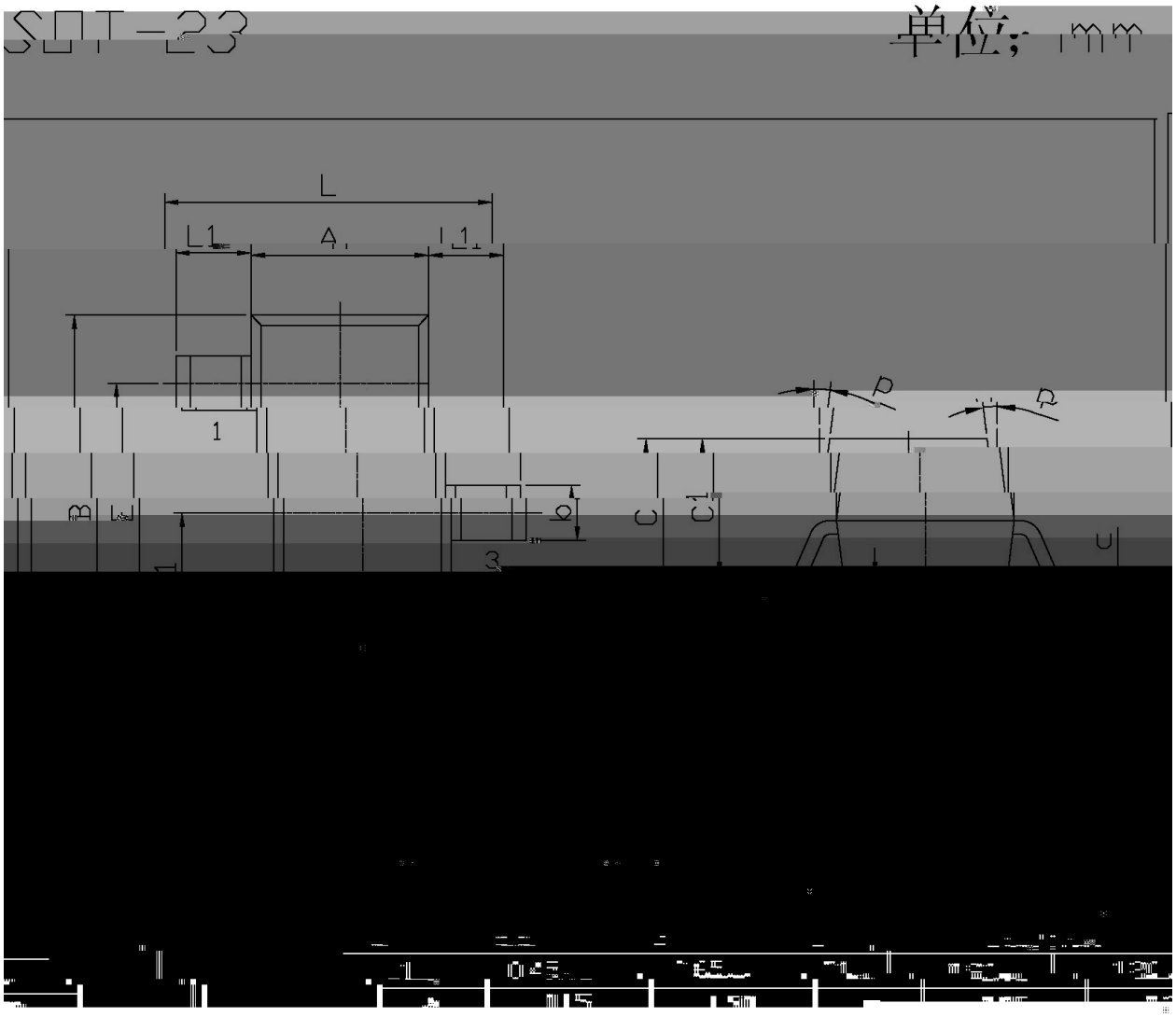
ㅈ ɔ ǁ ɯ ` ı Ḥ $V_{CE(sat)}$
High current gain, Low collector-emitter saturation voltage.

[illegible]

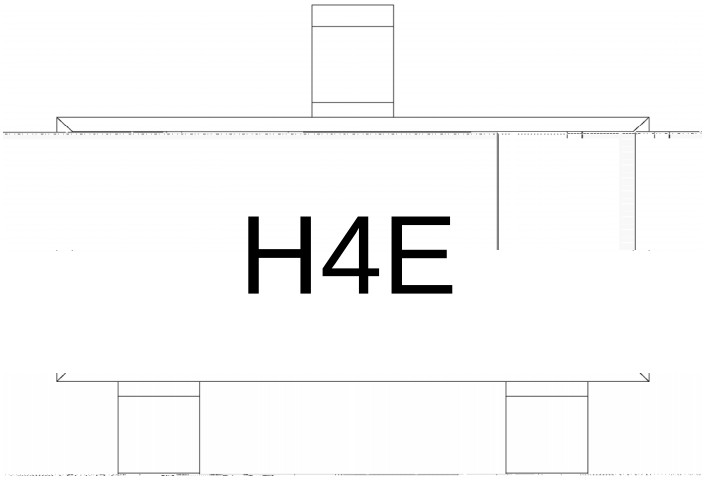
v ̈Ω̣ Parameter	ɬ N Symbol	̈Ω̣Ö Rating	D Ɉ Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω̣ Parameter	ɬ N Symbol	⊥⊥ ;ɬ ʈ Test Conditions	ω̣ ṇ Ö Min	Ɛ ʒ Ö Typ	ω̣ ʑ Ö Max	D Ɉ Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-10mA I_B=0	-45			V
Collector to Base Breakdown Voltage	V_{CBO}	I_CC I	E		O	

/ Package Dimensions



/ Marking Instructions



ب ˝ χ

K χ ⌘ ⅔ ᴵ Ɱ

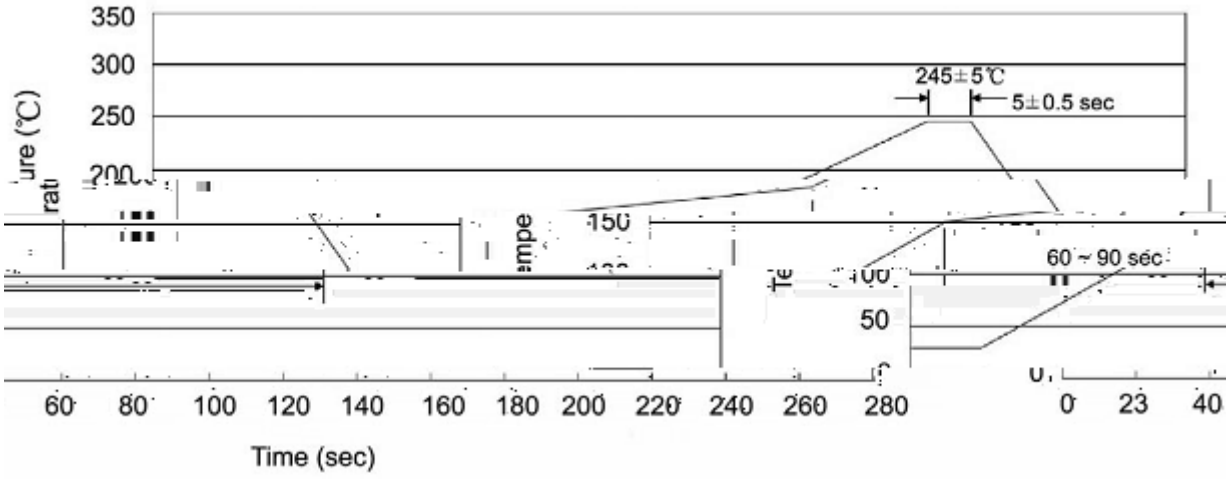
7H χ ⌘ ⅔ ᴺ Ɱ

Note:

H: Company Code.

4E: Product Type Code

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ

1 ⺊ ♬ □ ỷ 25 Ḱ 150 ɫ ı `H ڑ 60 Ḱ 90sec;

2 Š Ö □ ỷ 245 ° 5 ɫ ı `H ڑ ˋY ⺈ ⺧ 5 ° 0.5sec;

3 ì ˙ ⺈ ˛ ɔ ⺌ ỷ ⺧ 2 Ḱ 10 ɫ /sec.

Note:

1.Preheating:25~150 ɫ , Time:60~90sec.

2.Peak Temp.:245 ° 5 ɫ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɫ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 260±5 `H ڑ χ 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

ɔ` γ ⺊ / REEL

Package Type	Units					Dimension (unit mm^3)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ Notices